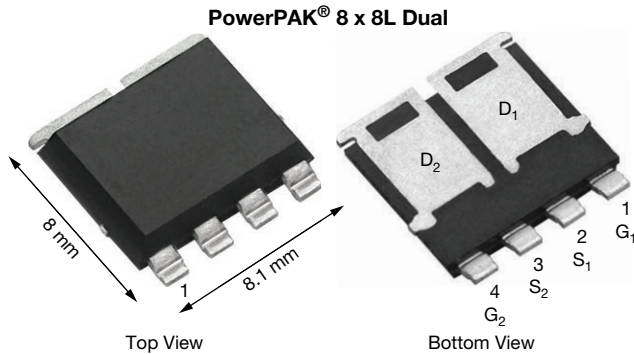


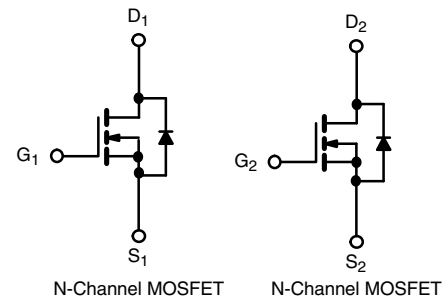
Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFET



FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Fully lead (Pb)-free device
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912

PRODUCT SUMMARY	
V _{DS} (V)	40
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.0039
R _{DS(on)} (Ω) at V _{GS} = 4.5 V	0.0047
I _D (A) per leg	100
Configuration	Dual
Package	PowerPAK 8 x 8L



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V _{DS}	40	V
Gate-source voltage	V _{GS}	± 20	
Continuous drain current	I _D	T _C = 25 °C ^a	100
		T _C = 125 °C	60
Continuous source current (diode conduction) ^a	I _S	68	A
Pulsed drain current ^b	I _{DM}	400	
Single pulse avalanche current	I _{AS}	50	
Single pulse avalanche energy	E _{AS}	125	mJ
Maximum power dissipation ^b	P _D	T _C = 25 °C	
		T _C = 125 °C	25
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R _{thJA}	80	°C/W
Junction-to-case (drain)	R _{thJC}	2	

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$	40	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.5	2	2.5	
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0\text{ V}$ $V_{DS} = 20\text{ V}$	-	-	1	μA
		$V_{GS} = 0\text{ V}$ $V_{DS} = 40\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$ $V_{DS} = 40\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	150	
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$ $V_{DS} \geq 5\text{ V}$	40	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ $I_D = 20\text{ A}$	-	0.0034	0.0039	Ω
		$V_{GS} = 4.5\text{ V}$ $I_D = 10\text{ A}$	-	0.0039	0.0047	
		$V_{GS} = 10\text{ V}$ $I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.0074	
		$V_{GS} = 10\text{ V}$ $I_D = 20\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.0091	
Forward transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$	-	105	-	S
Dynamic ^b						
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$ $V_{DS} = 20\text{ V}, f = 1\text{ MHz}$	-	4695	5900	μF
Output capacitance	C_{oss}		-	637	800	
Reverse transfer capacitance	C_{rss}		-	259	330	
Total gate charge ^c	Q_g	$V_{GS} = 10\text{ V}$ $V_{DS} = 20\text{ V}, I_D = 40\text{ A}$	-	85	120	nC
Gate-source charge ^c	Q_{gs}		-	10	-	
Gate-drain charge ^c	Q_{gd}		-	12	-	
Gate resistance	R_g	$f = 1\text{ MHz}$	0.7	1.5	3.0	Ω
Turn-on delay time ^c	$t_{d(on)}$	$V_{DD} = 20\text{ V}, R_L = 0.5\text{ }\Omega$ $I_D \cong 40\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$	-	14	30	ns
Rise time ^c	t_r		-	7.5	15	
Turn-off delay time ^c	$t_{d(off)}$		-	30	60	
Fall time ^c	t_f		-	14	30	
Source-Drain Diode Ratings and Characteristics ^b						
Pulsed current ^a	I_{SM}		-	-	200	A
Forward voltage	V_{SD}	$I_F = 40\text{ A}, V_{GS} = 0$	-	1	1.2	V

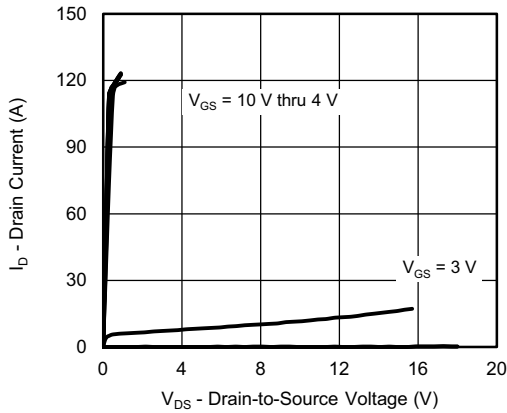
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

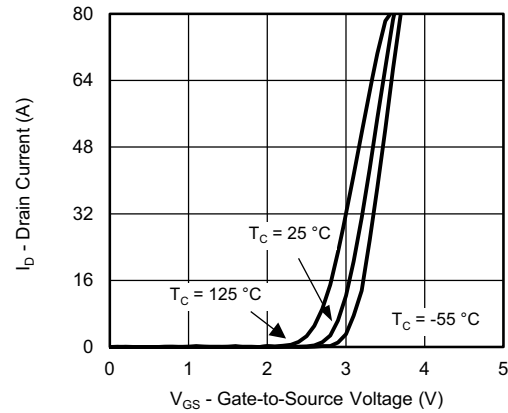
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.



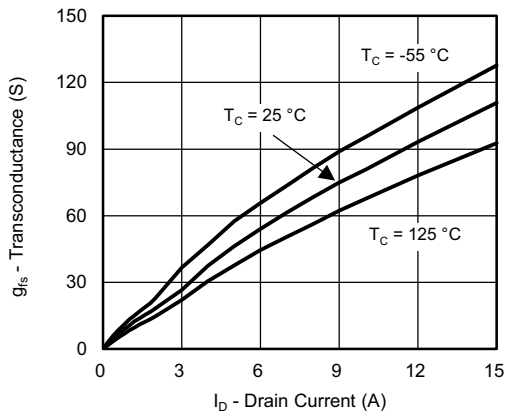
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



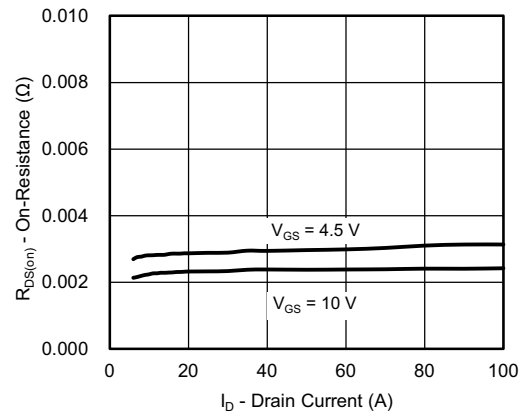
Output Characteristics



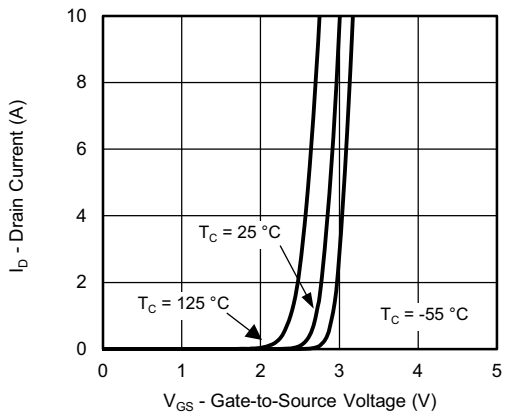
Transfer Characteristics



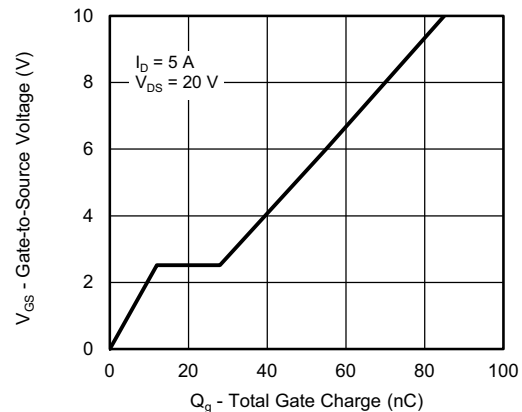
Transconductance



On-Resistance vs. Drain Current



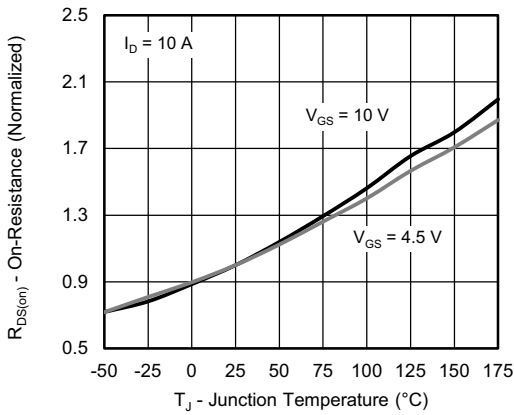
Transfer Characteristics



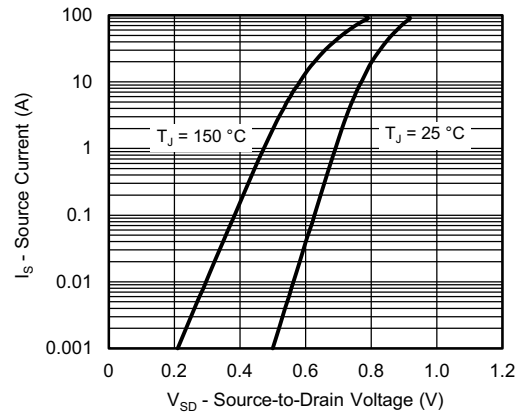
Gate Charge



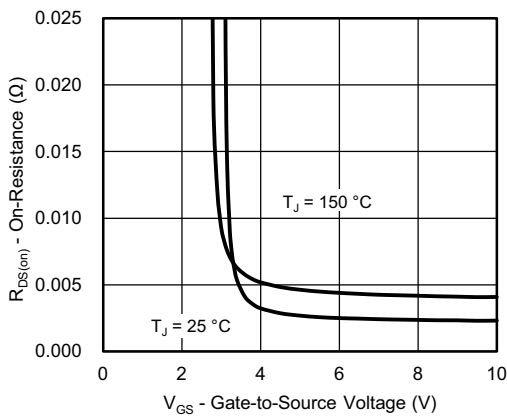
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



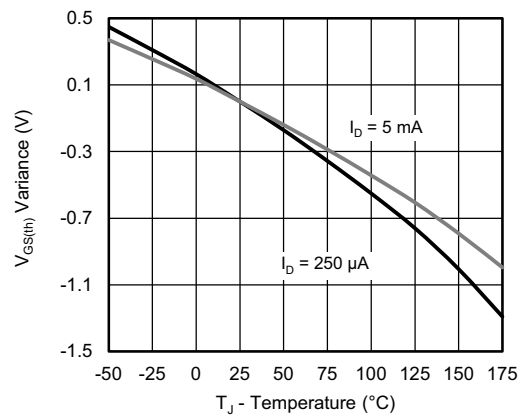
On-Resistance vs. Junction Temperature



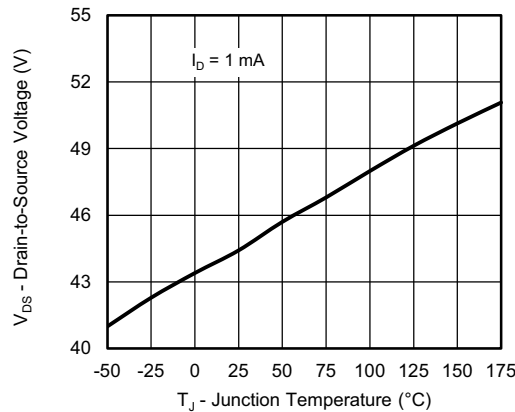
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



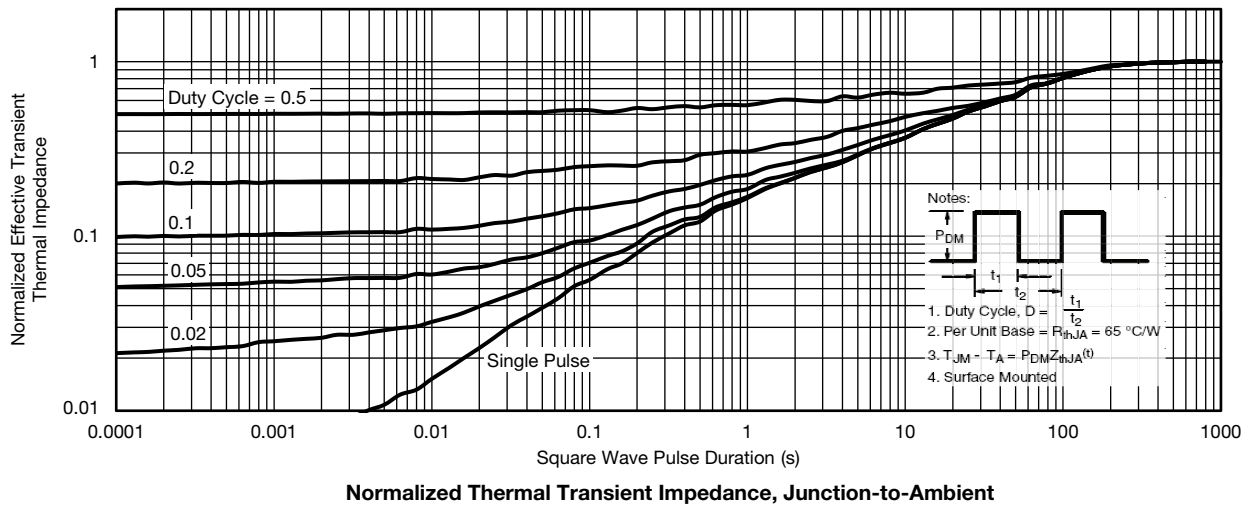
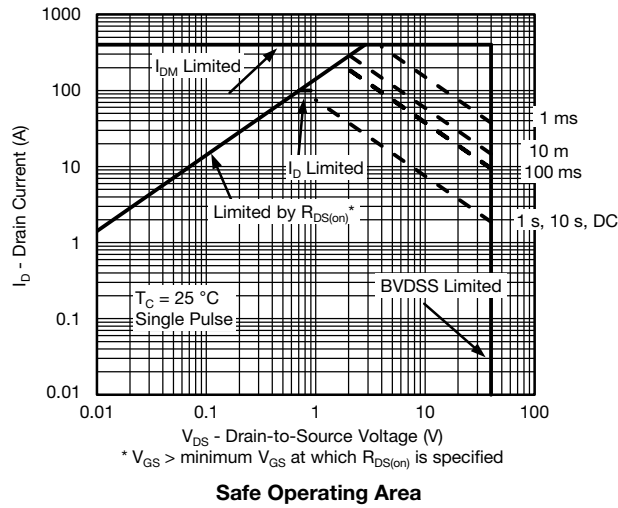
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

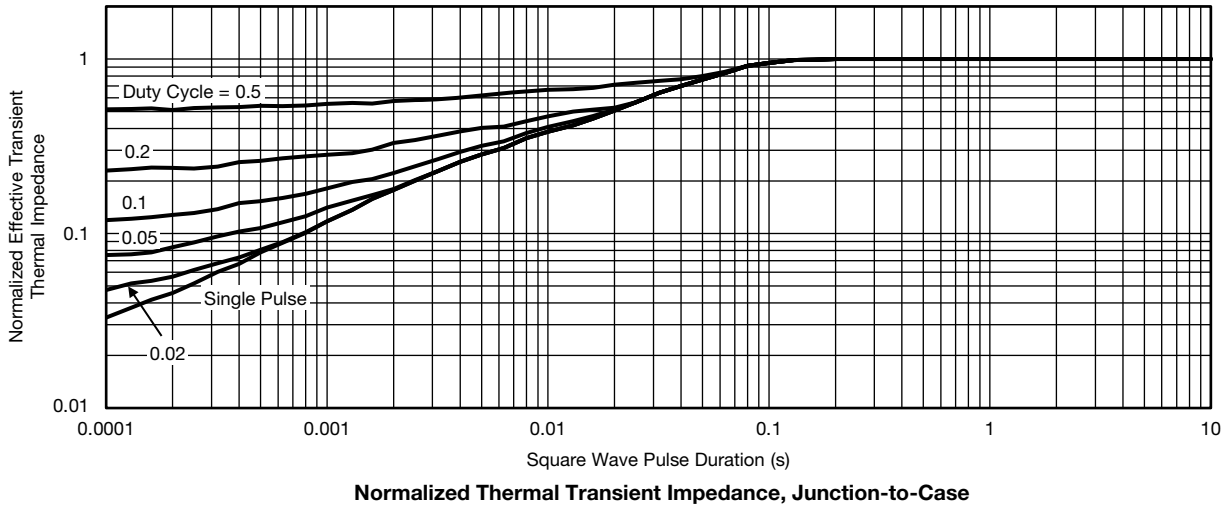


THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)





THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



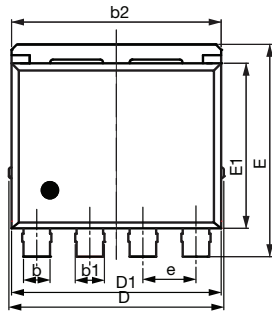
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

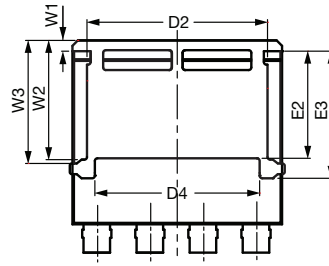
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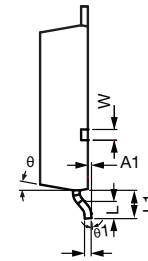
PowerPAK[®] 8 x 8L Case Outline



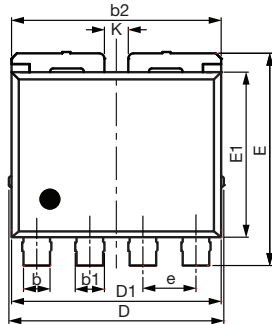
Top view (single)



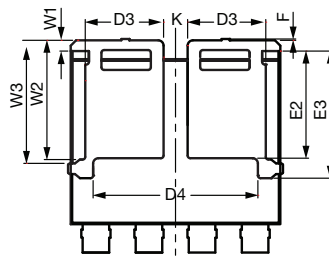
Bottom view (single)



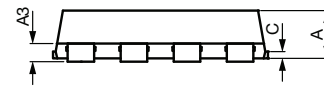
0.25 gauge line



Top view (dual)



Bottom view (dual)

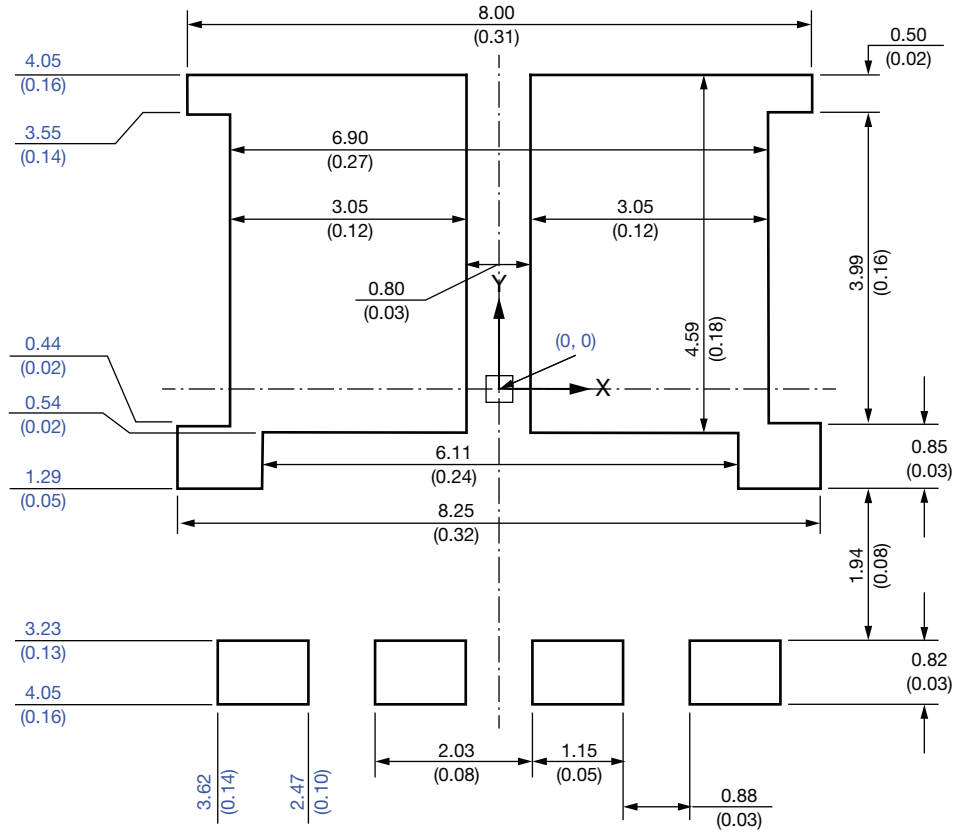


DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.70	1.80	1.90	0.067	0.071	0.075
A1	0.00	0.08	0.13	0.000	0.003	0.005
A3	0.55	0.62	0.70	0.022	0.024	0.028
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	7.80	7.90	8.00	0.307	0.311	0.315
c	0.20	0.25	0.30	0.008	0.010	0.012
D	8.00	8.10	8.25	0.315	0.319	0.325
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D3	2.85	2.95	3.05	0.112	0.116	0.120
D4	6.11	6.21	6.31	0.241	0.244	0.248
e	1.95	2.00	2.05	0.077	0.079	0.081
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	3.94	4.04	4.14	0.140	0.159	0.163
E3	4.69	4.79	4.89	0.185	0.189	0.193
F	0.05	0.10	0.15	0.002	0.004	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.80	0.90	1.00	0.031	0.035	0.039
W	0.30	0.40	0.50	0.012	0.016	0.020
W1	0.30	0.40	0.50	0.012	0.016	0.020
W2	4.39	4.49	4.59	0.173	0.177	0.181
W3	4.54	4.64	4.74	0.179	0.183	0.187
θ	6°	10°	14°	6°	10°	14°
θ1	0°	3°	8°	0°	3°	8°

C14-0891-Rev. A, 06-Oct-14
DWG: 6026



Recommended Minimum PADs for PowerPAK® 8 x 8L Dual



Dimensions in millimeters (inches)

Note

- Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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